

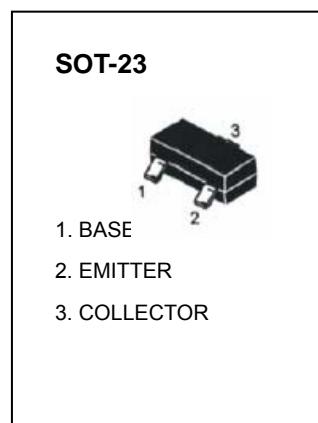


JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

2SA1037 TRANSISTOR (PNP)**FEATURES**

- Excellent h_{FE} linearity.
- Complements the 2SC2412

MARKING : FQ, FR, FS**MAXIMUM RATINGS (T_A=25°C unless otherwise noted)**

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current -Continuous	150	mA
P _c	Collector Power Dissipation	200	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-50μA,I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA,I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-50μA,I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-60V,I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V,I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-6V,I _C =-1mA	120		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-50mA,I _B =-5mA			-0.5	V
Transition frequency	f _T	V _{CE} =-12V,I _C =-2mA,f=30MHz		140		MHz
Collector output capacitance	C _{ob}	V _{CB} =-12V,I _E =0,f=1MHz		4.0	5.0	pF

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120 - 270	180 - 390	270 - 560

Typical Characteristics

2SA1037

●Electrical characteristic curves

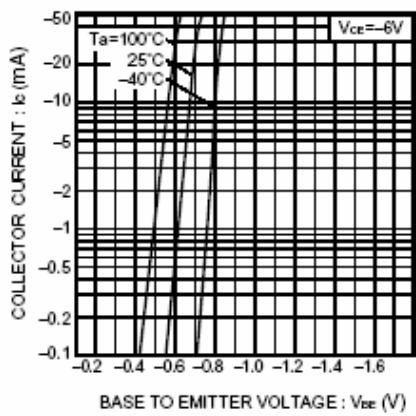


Fig.1 Grounded emitter propagation characteristics

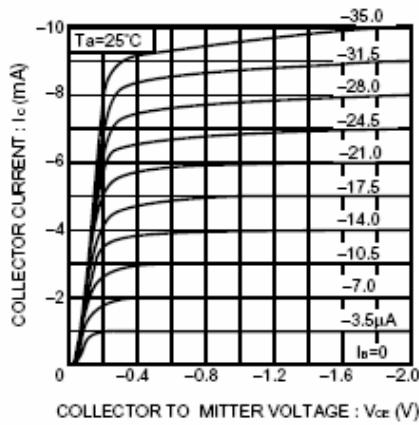


Fig.2 Grounded emitter output characteristics (I)

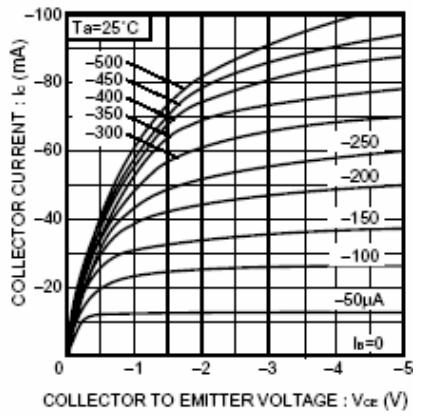


Fig.3 Grounded emitter output characteristics (II)

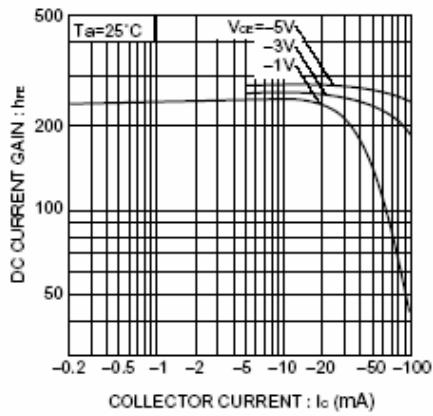


Fig.4 DC current gain vs. collector current (I)

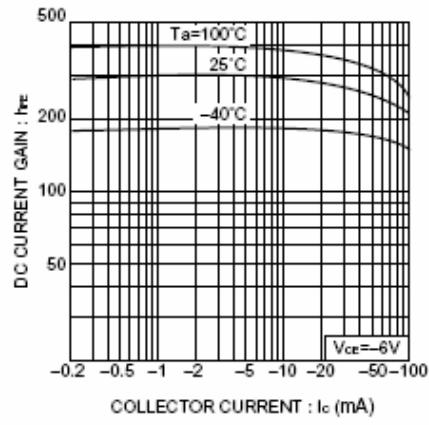


Fig.5 DC current gain vs. collector current (II)

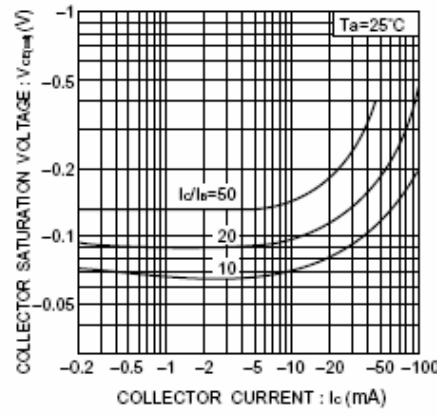


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

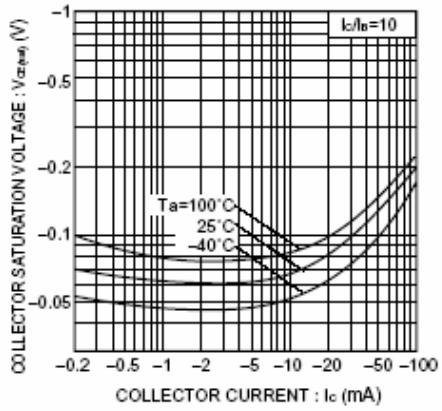


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

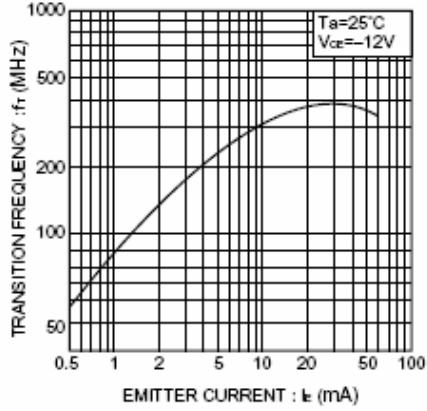


Fig.8 Gain bandwidth product vs. emitter current

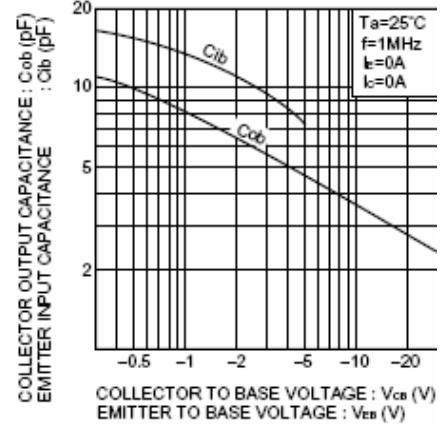


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage